

Standard Rectifier Module

$$V_{RRM} = 2 \times 1600 \text{ V}$$

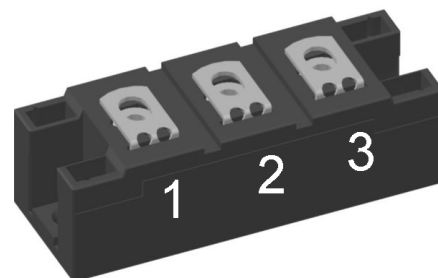
$$I_{FAV} = 210 \text{ A}$$

$$V_F = 1.04 \text{ V}$$

Phase leg

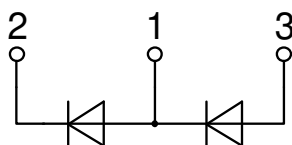
Part number

MDMA210P1600YD



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: Y4

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

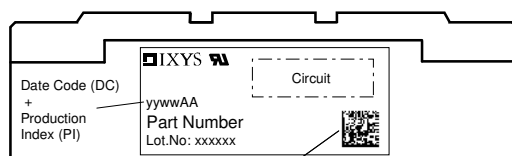
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_R	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	mA
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			15	mA
V_F	forward voltage drop	$I_F = 210\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.13	V
		$I_F = 420\text{ A}$				1.34	V
		$I_F = 210\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.04	V
		$I_F = 420\text{ A}$				1.30	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ d = 0.5			210	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.76	V
r_F	slope resistance					1.2	mΩ
R_{thJC}	thermal resistance junction to case					0.17	K/W
R_{thCH}	thermal resistance case to heatsink				0.09		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				735	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			6.60	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			7.13	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			5.61	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			6.06	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			217.8	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			211.5	kA ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			157.4	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			152.8	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			208		pF

Package Y4				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				300	A
T _{VJ}	virtual junction temperature			-40		150	°C
T _{op}	operation temperature			-40		125	°C
T _{stg}	storage temperature			-40		125	°C
Weight					150		g
M _D	mounting torque			2.25		2.75	Nm
M _T	terminal torque			4.5		5.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0			mm
d _{Spb/Apb}		terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	4800			V
		t = 1 minute		4000			V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Part description

M = Module
 D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 210 = Current Rating [A]
 P = Phase leg
 1600 = Reverse Voltage [V]
 YD = Y4-M6

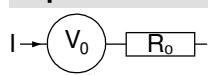
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDMA210P1600YD	MDMA210P1600YD	Box	6	517762

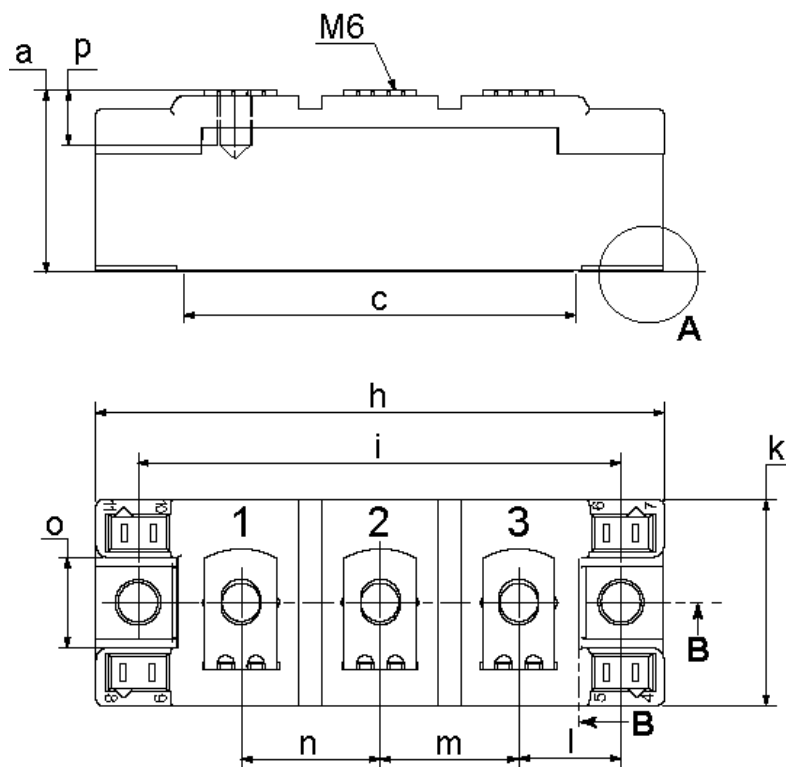
Similar Part	Package	Voltage class
MDMA180P1600YD	Y4-M6	1600
MDMA280P1600YD	Y4-M6	1600

Equivalent Circuits for Simulation

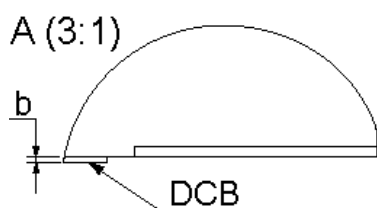
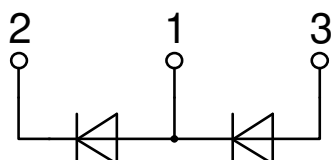
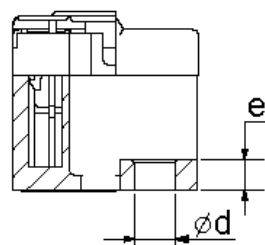
* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Rectifier	
$V_{0\max}$	threshold voltage	0.76	V
$R_{0\max}$	slope resistance *	0.57	mΩ

Outlines Y4


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	


B-B (1:1)


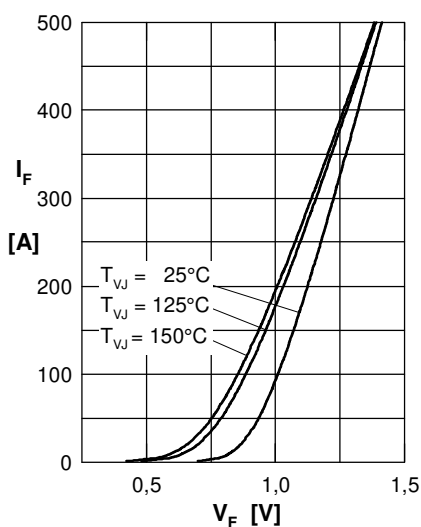
Rectifier


Fig. 1 Forward current versus voltage drop per diode

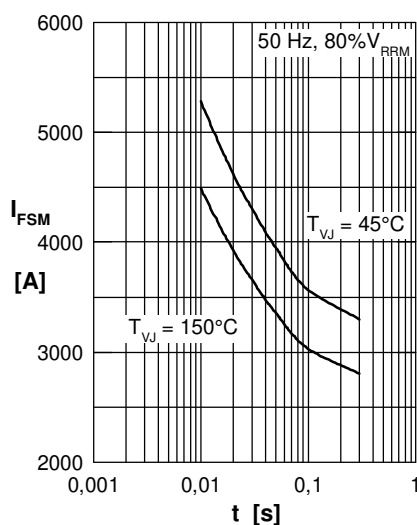


Fig. 2 Surge overload current vs. time per diode

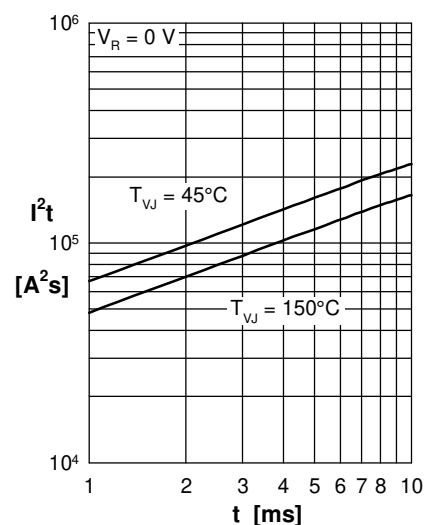
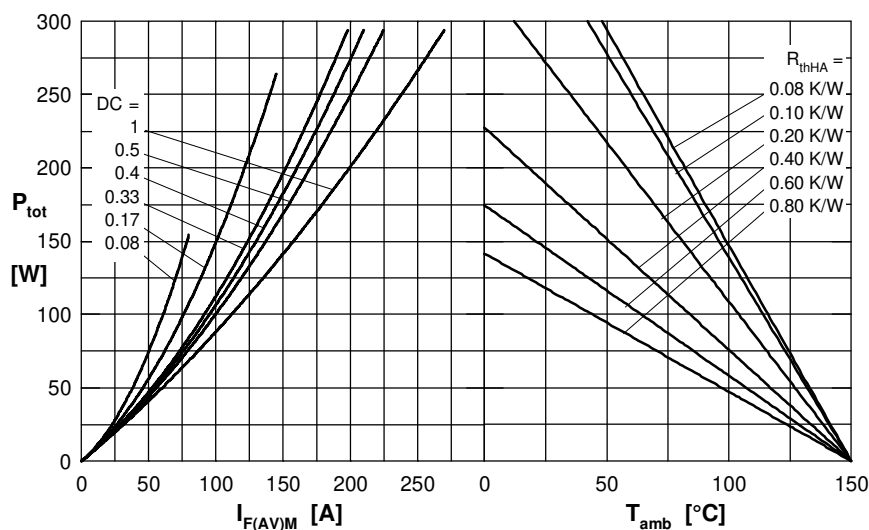

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

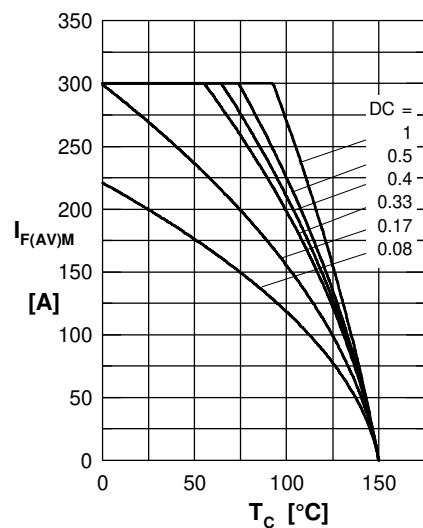


Fig. 5 Max. forward current vs. case temperature per diode

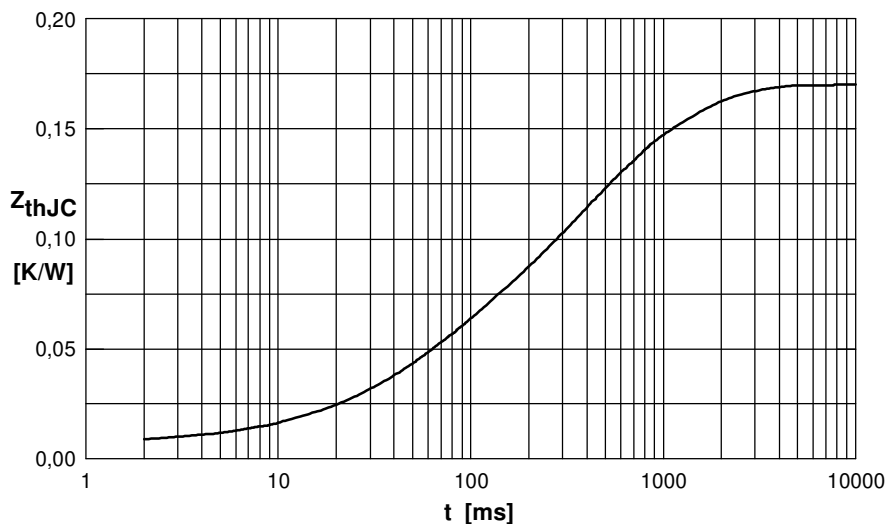


Fig. 6 Transient thermal impedance junction to case vs. time per diode

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.007	0.0005
2	0.036	0.0500
3	0.072	0.3000
4	0.055	1.0000